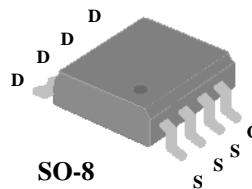




- ▼ Simple Drive Requirement
- ▼ Good Recovery Time
- ▼ Fast Switching Performance
- ▼ RoHS Compliant & Halogen-Free

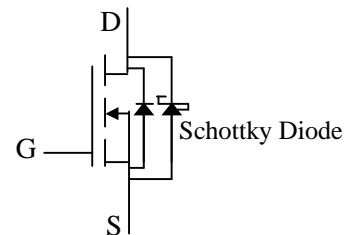


BV_{DSS}	30V
$R_{DS(ON)}$	9m Ω
I_D	13A

Description

AP4813 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The SO-8 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for voltage conversion or switch applications.



Absolute Maximum Ratings @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ\text{C}$	Drain Current, $V_{GS} @ 10V^3$	13	A
$I_D @ T_A=70^\circ\text{C}$	Drain Current, $V_{GS} @ 10V^3$	10.6	A
I_{DM}	Pulsed Drain Current ¹	50	A
V_{KA}	Schottky Reverse Voltage	30	V
$I_F @ T_A=25^\circ\text{C}$	Forward Current	1	A
I_{FM}	Pulsed Diode Forward Current	25	A
$P_D @ T_A=25^\circ\text{C}$	Max Power Dissipation (MOSFET)	2.5	W
	Max Power Dissipation (Schottky)	2.0	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³ (MOSFET)	50	$^\circ\text{C}/\text{W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³ (Schottky)	60	$^\circ\text{C}/\text{W}$



AP4813GSM-HF

Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=12A$	-	-	9	$m\Omega$
		$V_{GS}=4.5V, I_D=8A$	-	-	15	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=8A$	-	20	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V$	-	-	100	μA
	Drain-Source Leakage Current ($T_j=70^{\circ}\text{C}$)	$V_{DS}=24V, V_{GS}=0V$	-	-	1	mA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Q_g	Total Gate Charge	$I_D=8A$	-	11.5	18	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=15V$	-	2.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	7	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V$	-	9	-	ns
t_r	Rise Time	$I_D=1A$	-	7	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	23	-	ns
t_f	Fall Time	$R_D=15\Omega$	-	8	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	730	1170	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	205	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	150	-	pF
R_g	Gate Resistance	$f=1.0\text{MHz}$	-	1.5	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Diode+Schottky Forward On Voltage ²	$I_S=1.0A, V_{GS}=0V$	-	0.48	0.5	V
t_{rr}	Body Diode+Schottky Reverse Recovery Time	$I_S=8A, V_{GS}=0V,$	-	20	-	ns
Q_{rr}	Body Diode+Schottky Reverse Recovery Charge	$di/dt=100A/\mu s$	-	9	-	nC

Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse test
3. Surface mounted on 1 in² copper pad of FR4 board, $t \leq 10$ sec.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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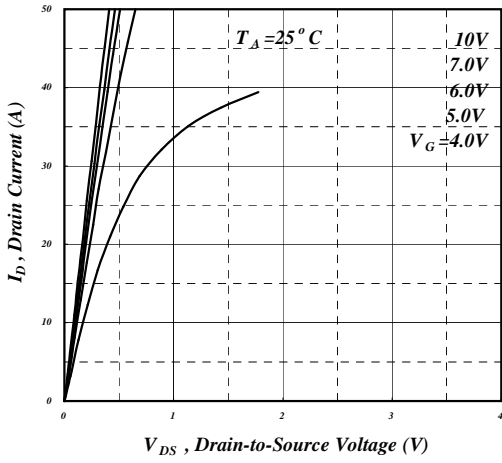


Fig 1. Typical Output Characteristics

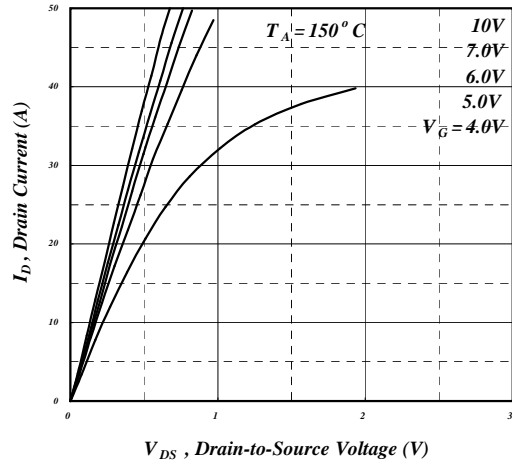


Fig 2. Typical Output Characteristics

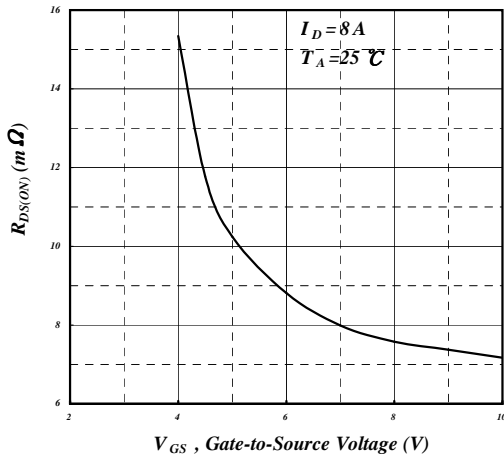


Fig 3. On-Resistance v.s. Gate Voltage

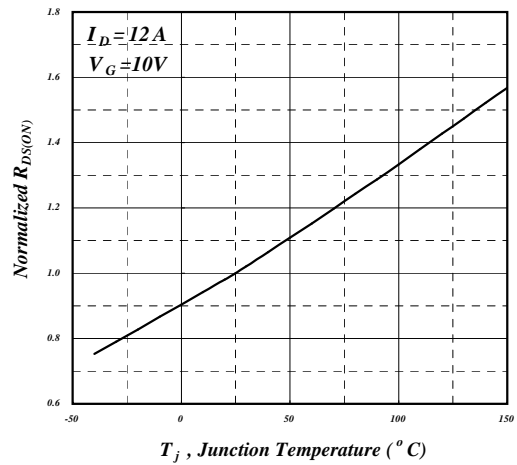


Fig 4. Normalized On-Resistance v.s. Junction Temperature

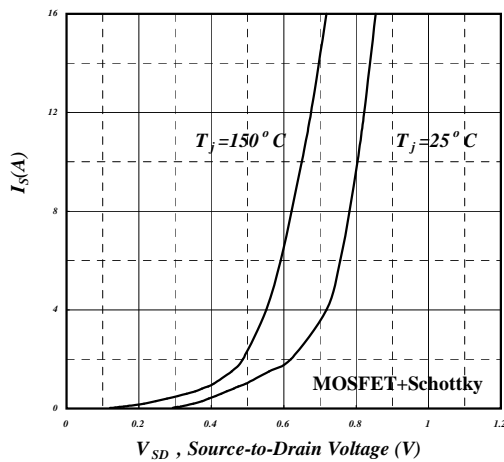


Fig 5. Forward Characteristic of Reverse Diode

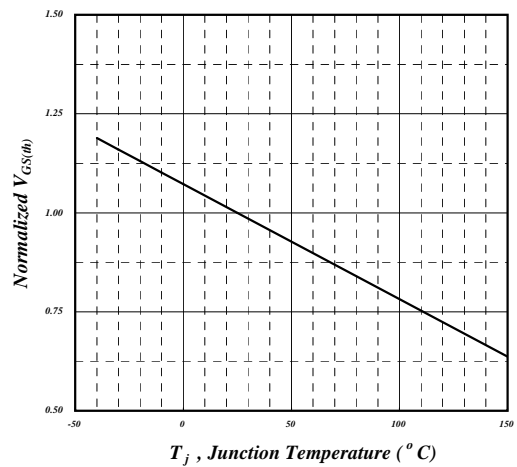


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

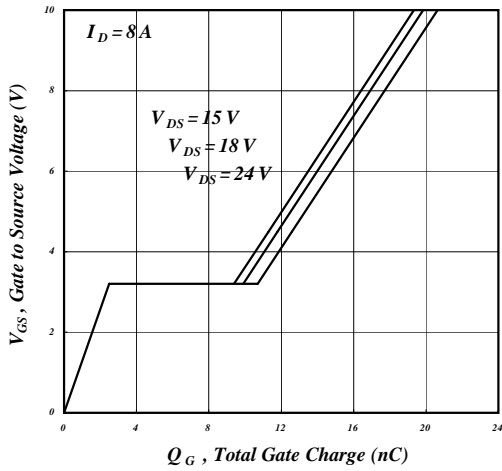


Fig 7. Gate Charge Characteristics

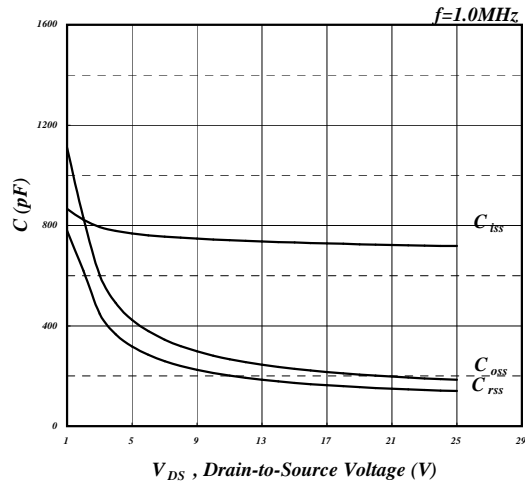


Fig 8. Typical Capacitance Characteristics

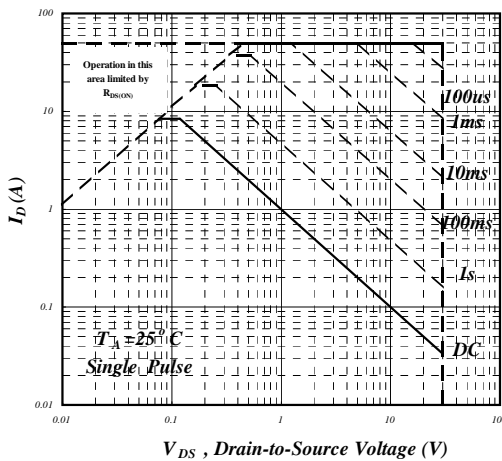


Fig 9. Maximum Safe Operating Area

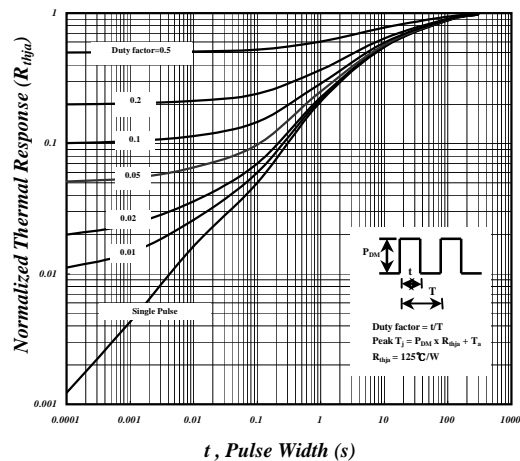


Fig 10. Effective Transient Thermal Impedance

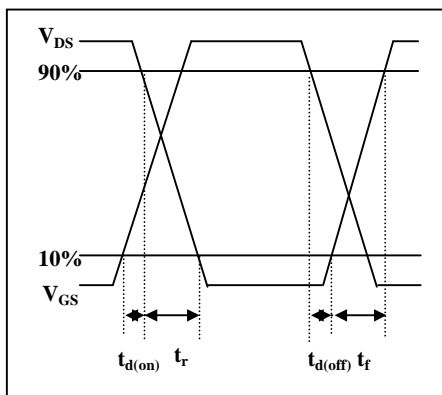


Fig 11. Switching Time Waveform

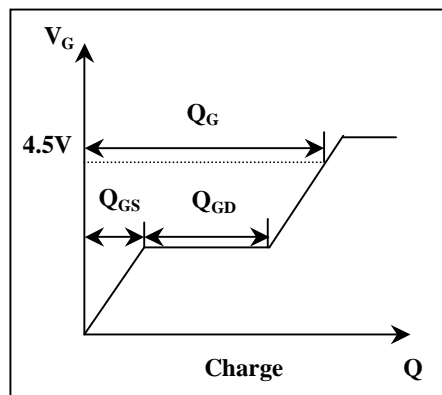


Fig 12. Gate Charge Waveform



MARKING INFORMATION

